



MCD02N60

N-Channel Enhancement Mode Field Effect Transistor

Features

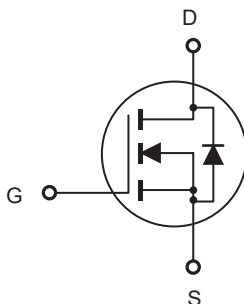
- Excellent stability and uniformity
- Extremely Low switching loss
- Lower $R_{dS(ON)}$
- Epoxy meets UL 94 V-0 flammability rating
- Moisture Sensitivity Level 1

Maximum Ratings @ 25°C Unless Otherwise Specified

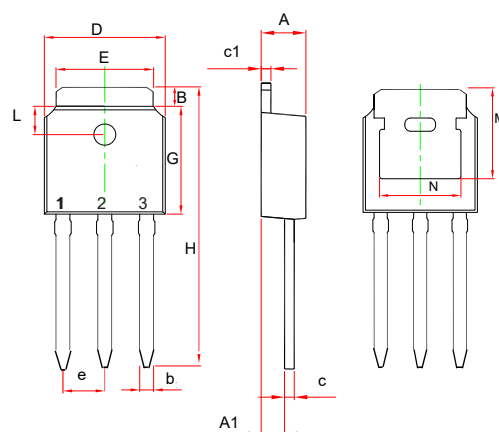
Symbol	Parameter	Rating	Unit
V_{DS}	Drain-source Voltage	600	V
I_D	Drain Current-Continuous ⁽¹⁾	2.0	A
I_D	Drain Current-Continuous@Tj=100°C ⁽¹⁾	1.25	A
I_D (pulse)	Drain Current-Pulsed ⁽²⁾	6.0	A
V_{GSS}	Gate-source Voltage	±30	V
E_{AS}	Single Pulsed Avalanche Energy ⁽⁴⁾	60	mJ
P_D	Power Dissipation ⁽³⁾	18	W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient ⁽⁵⁾	62	°C/W
T_J	Operating Junction Temperature	-55 to +150	°C
T_{STG}	Storage Temperature	-55 to +150	°C

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3) P_D is based on max. junction temperature, using junction-case thermal resistance.
- 4) $V_{DD}=50$ V, $R_G=25$ Ω , $L=20$ mH, starting $T_J=25$ °C
- 5) The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_a=25$ °C.

Internal Block Diagram



TO-251



- 1.GATE
- 2.DRAIN
- 3.SOURCE

DIM	DIMENSIONS				NOTE
	INCHES		MM		
A	.087	.094	2.20	2.40	
A1	.038	.054	0.97	1.17	
B	.035	.050	0.88	1.28	
b	.027	.035	0.68	0.90	
c	.017	.025	0.43	0.63	
c1	.017	.025	0.43	0.63	
D	.252	.268	6.40	6.80	
E	.205	.217	5.20	5.50	
G	.235	.245	5.98	6.22	
e	0.090BSC		2.286BSC		
H	.639	.662	16.22	16.82	
L	.065	.077	1.65	1.95	
M	0.209REF		5.30REF		
N	.182	---	4.63	---	

Electrical characteristics (T_a=25°C unless otherwise noted)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV _{DSS}	600			V	V _{GS} =0 V, I _D =250 μA
		650	750			V _{GS} =0 V, I _D =250 μA T _j =150 °C
Gate threshold voltage	V _{GS(th)}	2.0		4.0	V	V _{DS} =V _{GS} , I _D =250 μA
Drain-source on-state resistance	R _{DS(ON)}		1.9	2.2	Ω	V _{GS} =10 V, I _D =1 A
			4.8			V _{GS} =10 V, I _D =1 A, T _j =150 °C
Gate-source leakage current	I _{GSS}			100	nA	V _{GS} =30 V
				-100		V _{GS} =-30 V
Drain-source leakage current	I _{DSS}			1	μA	V _{DS} =600 V, V _{GS} =0 V
Dynamic Characteristics						
Input capacitance	C _{iss}		118		pF	V _{GS} =0 V, V _{DS} =50 V, f=1 MHz
Output capacitance	C _{oss}		12.5		pF	
Reverse transfer capacitance	C _{rss}		0.76		pF	
Turn-on delay time	t _{d(on)}		50.4		ns	V _{GS} =10 V, V _{DS} =380 V, R _G =25 Ω, I _D =2 A
Rise time	t _r		23.9		ns	
Turn-off delay time	t _{d(off)}		103.1		ns	
Fall time	t _f		44.7		ns	
Gate Charge Characteristics						
Total gate charge	Q _g		5.1		nC	I _D =2 A, V _{DS} =480 V, V _{GS} =10 V
Gate-source charge	Q _{gs}		1		nC	
Gate-drain charge	Q _{gd}		2.3		nC	
Gate plateau voltage	V _{plateau}		5.4		V	
Body Diode Characteristics						
Diode forward current	I _S			2	A	V _{GS} <V _{th}
Pulsed source current	I _{SP}			6		
Diode forward voltage	V _{SD}			1.4	V	I _S =2 A, V _{GS} =0 V
Reverse recovery time	t _{rr}		153.9		ns	V _R =400 V, I _S =2 A, di/dt=100 A/μs
Reverse recovery charge	Q _{rr}		0.617		μC	
Peak reverse recovery current	I _{rrm}		8.7		A	

■ Electrical Characteristics Diagrams

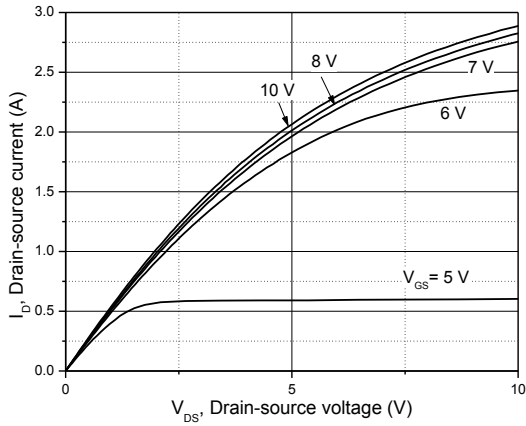


Figure 1, Typ. output characteristics

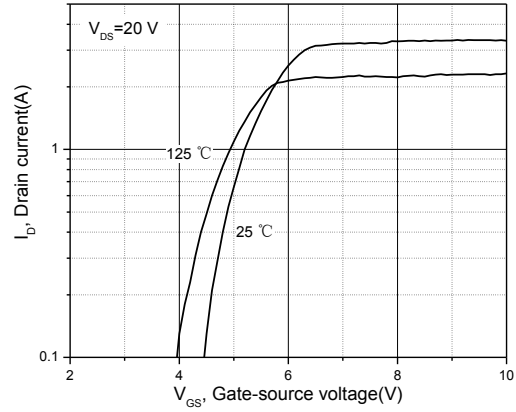


Figure 2, Typ. transfer characteristics

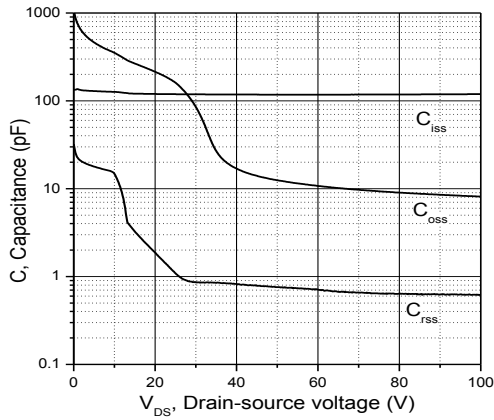


Figure 3, Typ. capacitances

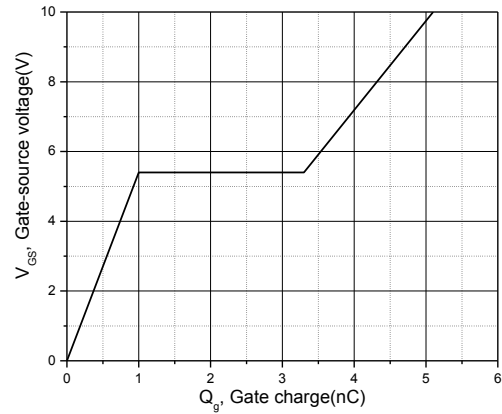


Figure 4, Typ. gate charge

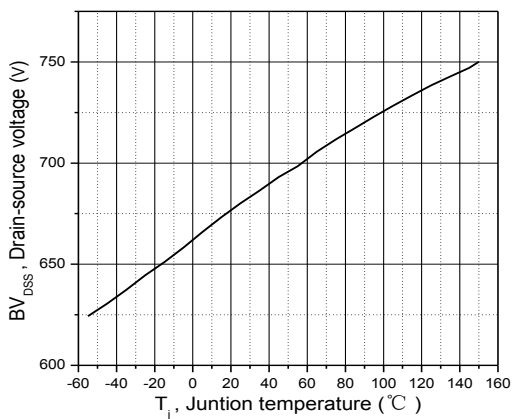


Figure 5, Drain-source breakdown voltage

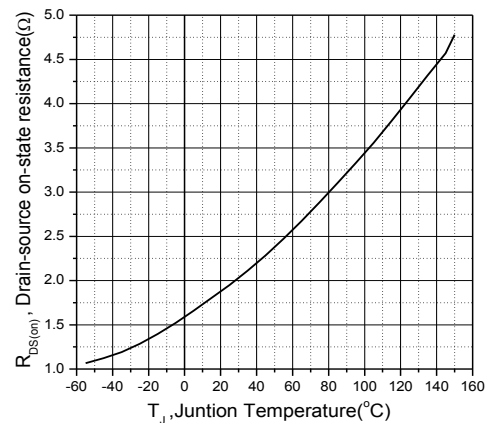


Figure 6, Drain-source on-state resistance

■ Electrical Characteristics Diagrams

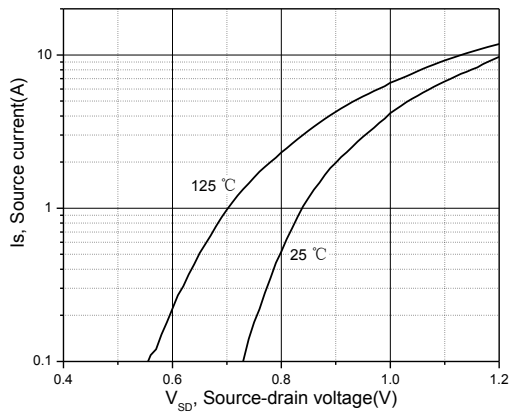


Figure 7, Forward characteristic of body diode

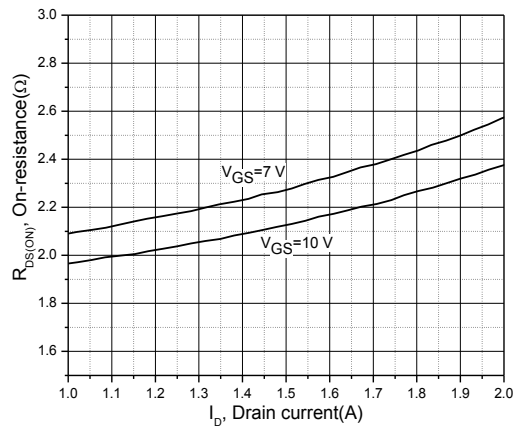


Figure 8, Drain-source on-state resistance

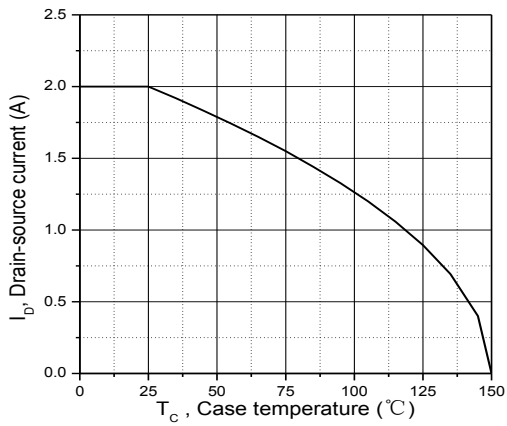


Figure 9, Drain current

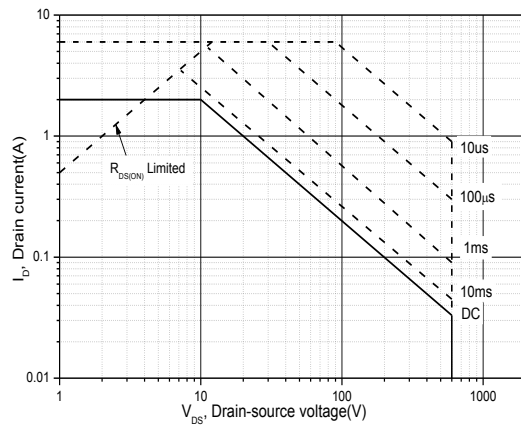


Figure 10, Safe operation area for $T_C=25\text{ }^\circ\text{C}$



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Ordering Information :

Device	Packing
Part Number-BP	Bulk:29.7Kpcs/Carton

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